

DMPH6050SPD-VB Datasheet

Dual P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY

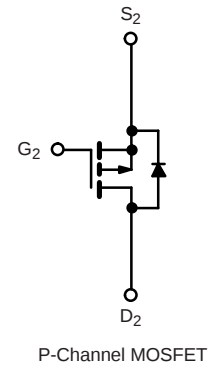
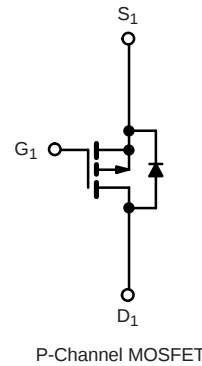
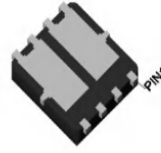
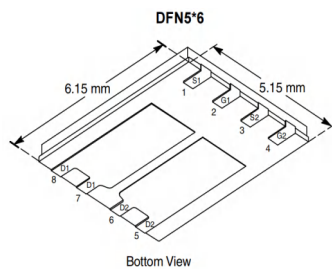
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^{d, e}	Q_g (Typ.)
- 60	0.060 at $V_{GS} = -10$ V	- 11	17 nC
	0.075 at $V_{GS} = -4.5$ V	- 9.5	

FEATURES

- Halogen-free
- Trench Power MOSFET
- 100 % UIS Tested

APPLICATIONS

- Load Switches



ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	I_D	$T_C = 25^\circ\text{C}$	A
		$T_C = 70^\circ\text{C}$	
		$T_A = 25^\circ\text{C}$	
		$T_A = 70^\circ\text{C}$	
Pulsed Drain Current	I_{DM}	- 33 ^e	A
Continuous Source-Drain Diode Current	I_S	$T_C = 25^\circ\text{C}$	
		$T_A = 25^\circ\text{C}$	
Avalanche Current	I_{AS}	- 20	mJ
Single-Pulse Avalanche Energy	E_{AS}	20	
Maximum Power Dissipation	P_D	$T_C = 25^\circ\text{C}$	W
		$T_C = 70^\circ\text{C}$	
		$T_A = 25^\circ\text{C}$	
		$T_A = 70^\circ\text{C}$	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, c}	R_{thJA}	38	50	$^\circ\text{C/W}$
Maximum Junction-to-Foot	R_{thJF}	20	25	

Notes:

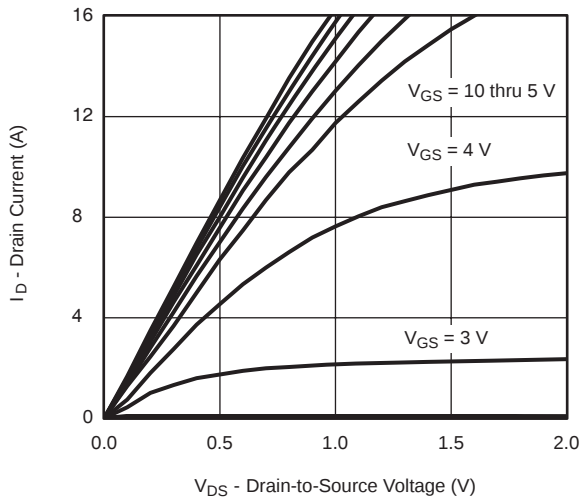
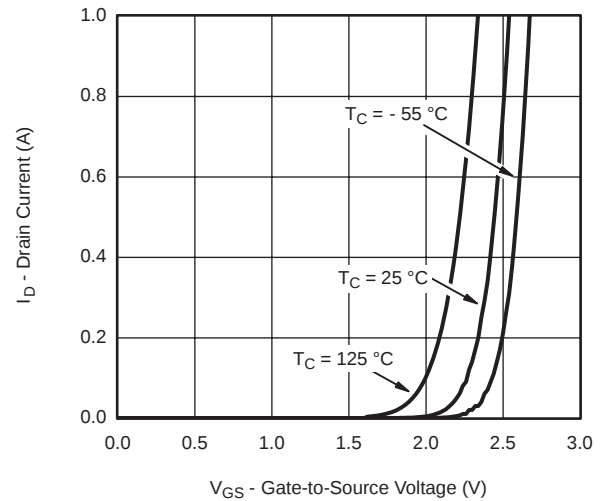
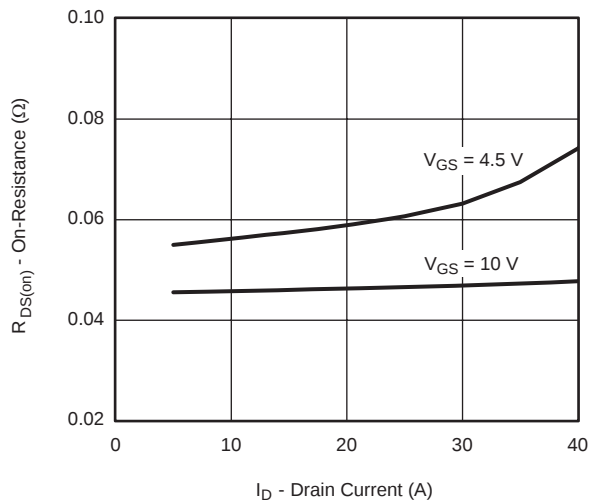
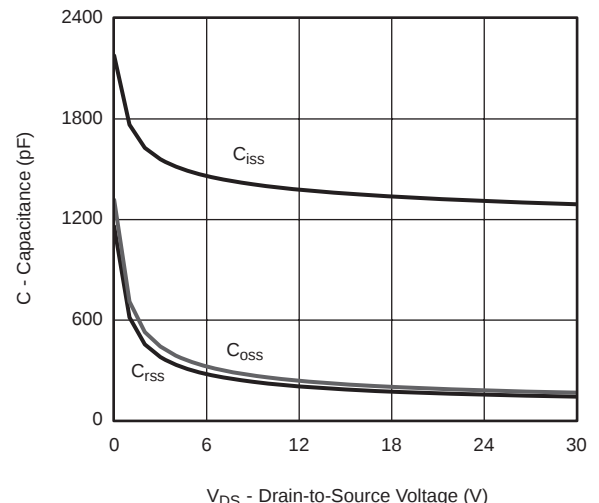
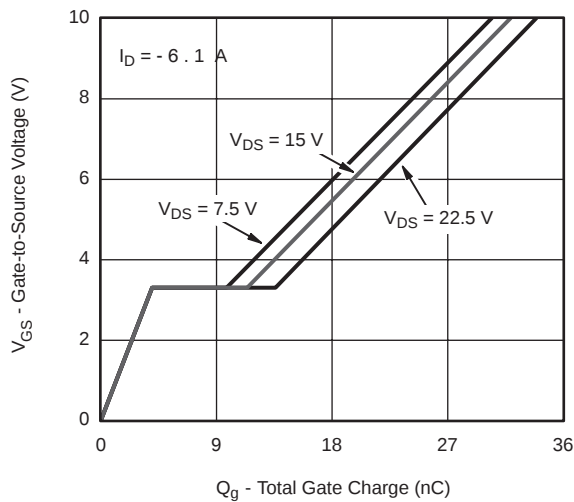
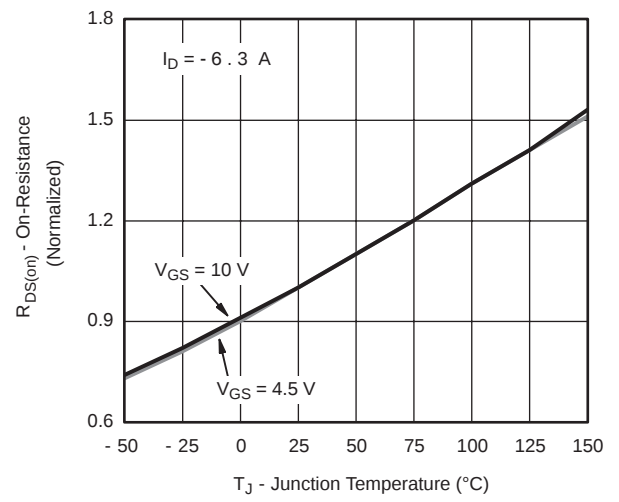
- Surface mounted on 1" x 1" FR4 board.
- $t = 10$ s.
- Maximum under Steady State conditions is 85°C/W .
- Based on $T_C = 25^\circ\text{C}$.
- Limited by package.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 60			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 31		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			4.5		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 1.0		- 3.0	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 55 °C			- 5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ - 10 V, V _{GS} = - 10 V	- 30			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 5 A		0.060		Ω
		V _{GS} = - 4.5 V, I _D = - 4.5 A		0.075		
Forward Transconductance ^a	g _{fs}	V _{DS} = - 10 V, I _D = - 5 A		23		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = - 15 V, V _{GS} = 0 V, f = 1 MHz		1500		pF
Output Capacitance	C _{oss}			210		
Reverse Transfer Capacitance	C _{rss}			180		
Total Gate Charge	Q _g	V _{DS} = - 15 V, V _{GS} = - 10 V, I _D = - 5 A		32	50	nC
		V _{DS} = - 15 V, V _{GS} = - 4.5 V, I _D = - 5 A		15	25	
Q _{gs}			4			
Q _{gd}			7.5			
Gate Resistance	R _g	f = 1 MHz		5.8		Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 15 V, R _L = 15 Ω I _D ≡ - 1 A, V _{GEN} = - 10 V, R _g = 1 Ω		10	15	ns
Rise Time	t _r			8	15	
Turn-Off DelayTime	t _{d(off)}			45	70	
Fall Time	t _f			12	25	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 15 V, R _L = 15 Ω I _D ≡ - 1 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		42	70	
Rise Time	t _r			35	60	
Turn-Off DelayTime	t _{d(off)}			40	70	
Fall Time	t _f			16	30	
Drain-Source Body Diode Characteristics						
Continous Source-Drain Diode Current	I _S	T _C = 25 °C			- 11	A
Pulse Diode Forward Current	I _{SM}				- 33	
Body Diode Voltage	V _{SD}	I _S = - 2 A, V _{GS} = 0 V		- 0.75	- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 2 A, dI/dt = 100 A/μs, T _J = 25 °C		34	60	ns
Body Diode Reverse Recovery Charge	Q _{rr}			22	40	nC
Reverse Recovery Fall Time	t _a			11		ns
Reverse Recovery Rise Time	t _b			23		

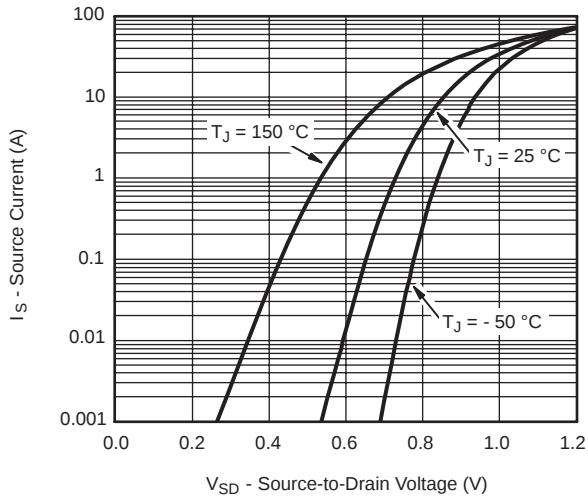
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

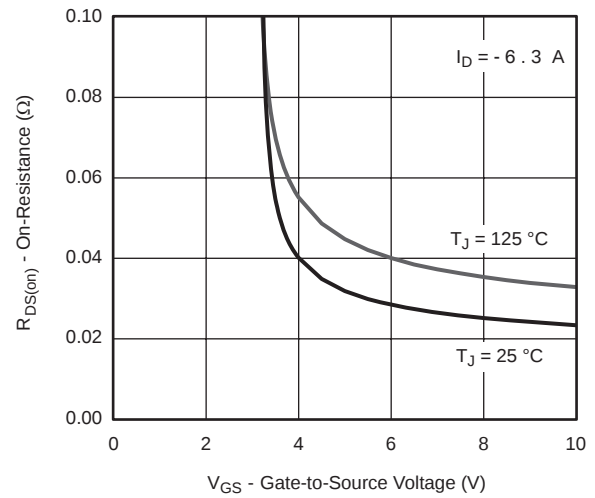
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

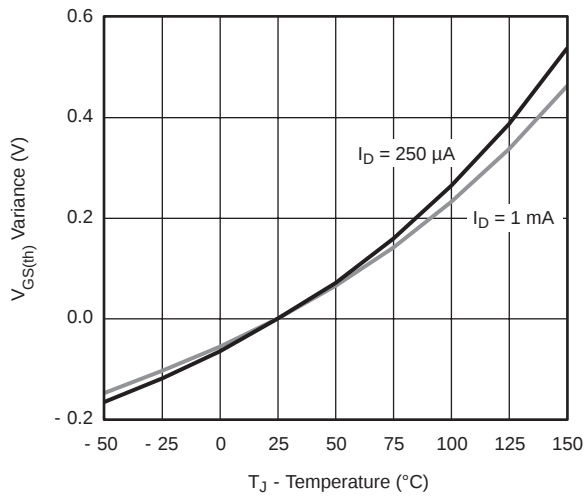
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



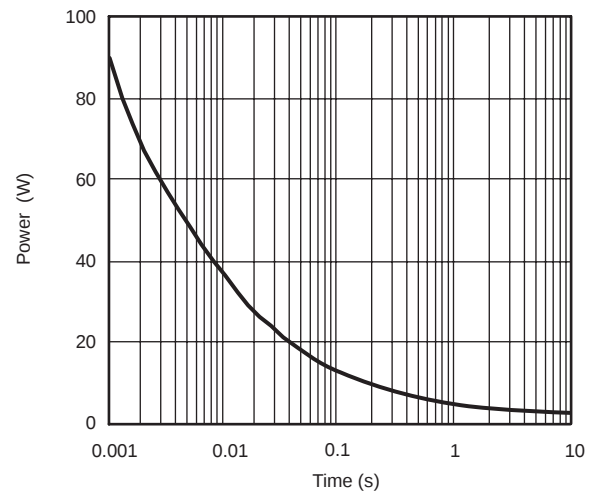
Source-Drain Diode Forward Voltage



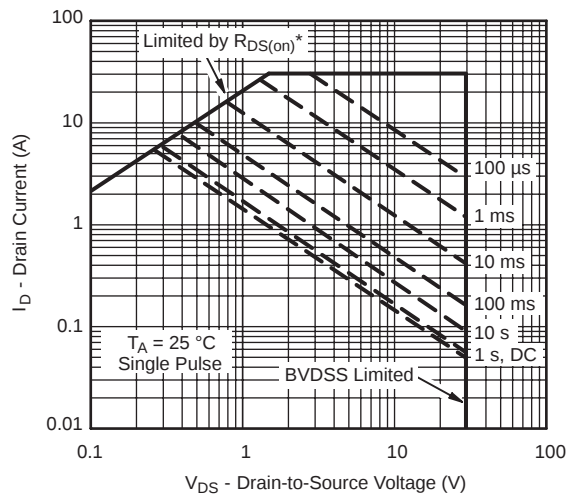
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



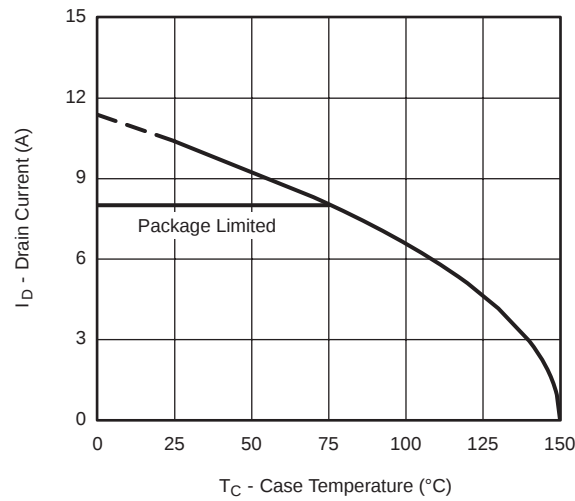
Single Pulse Power, Junction-to-Ambient



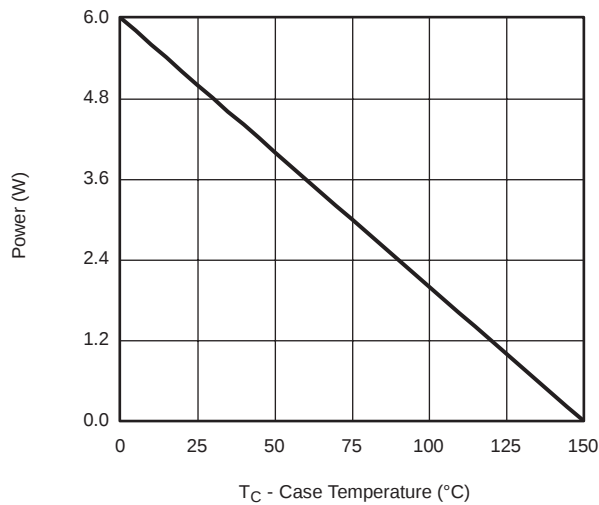
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

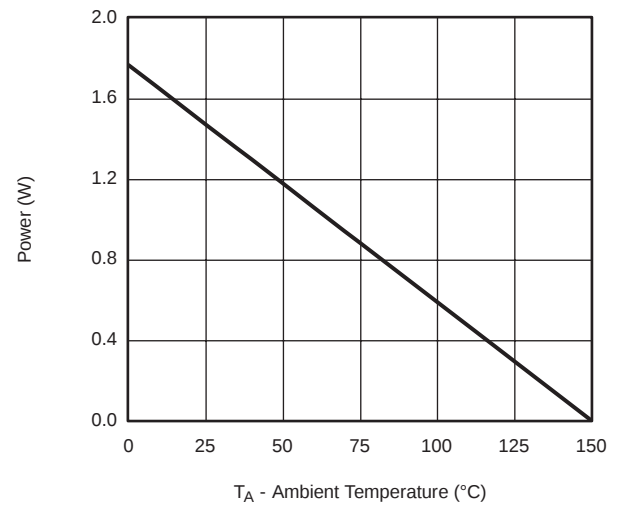
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*

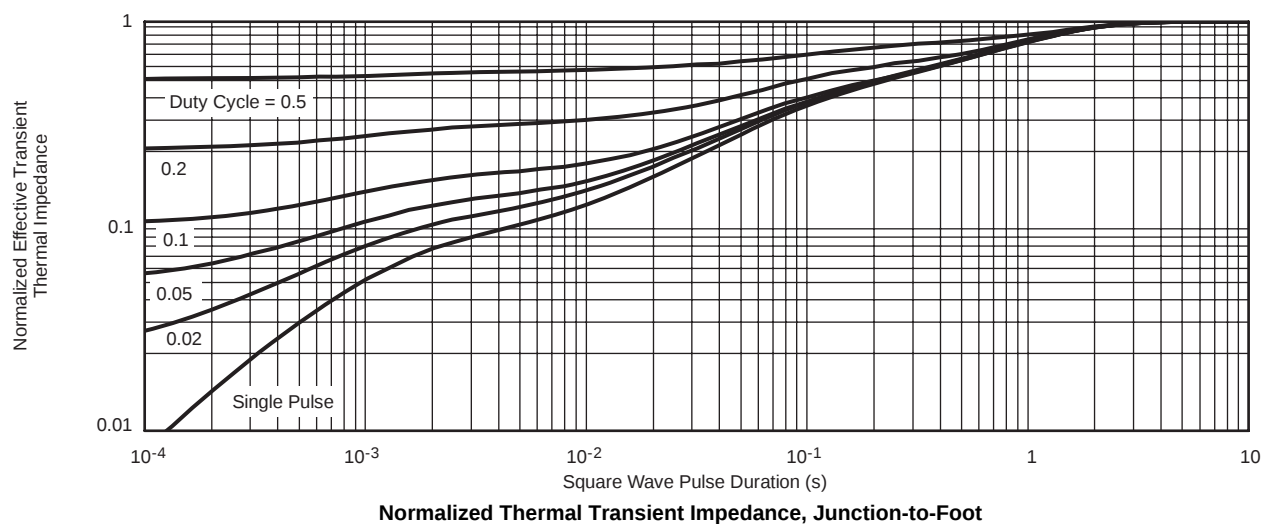
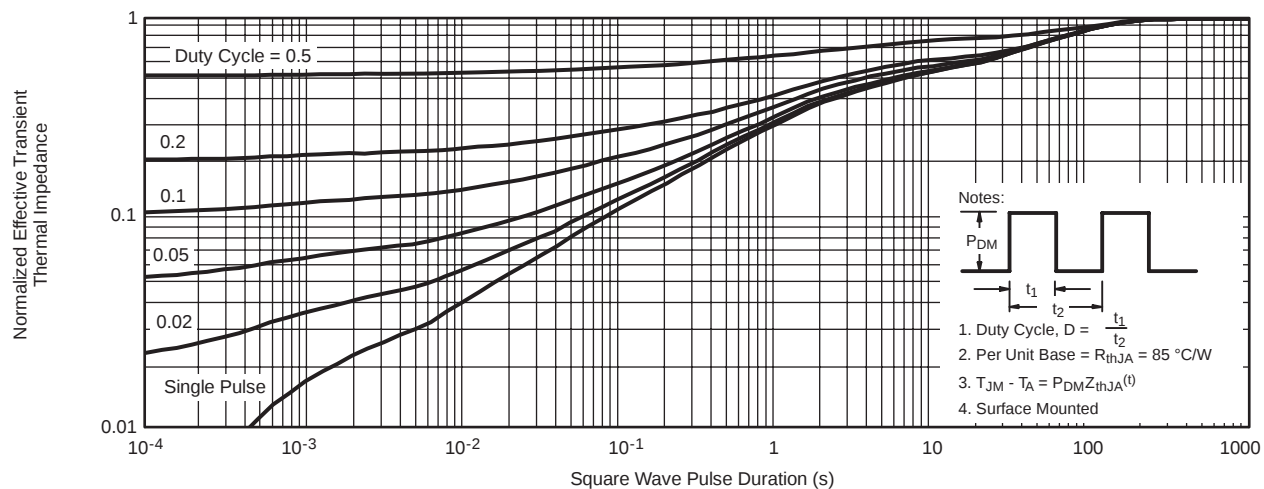


Power, Junction-to-Foot

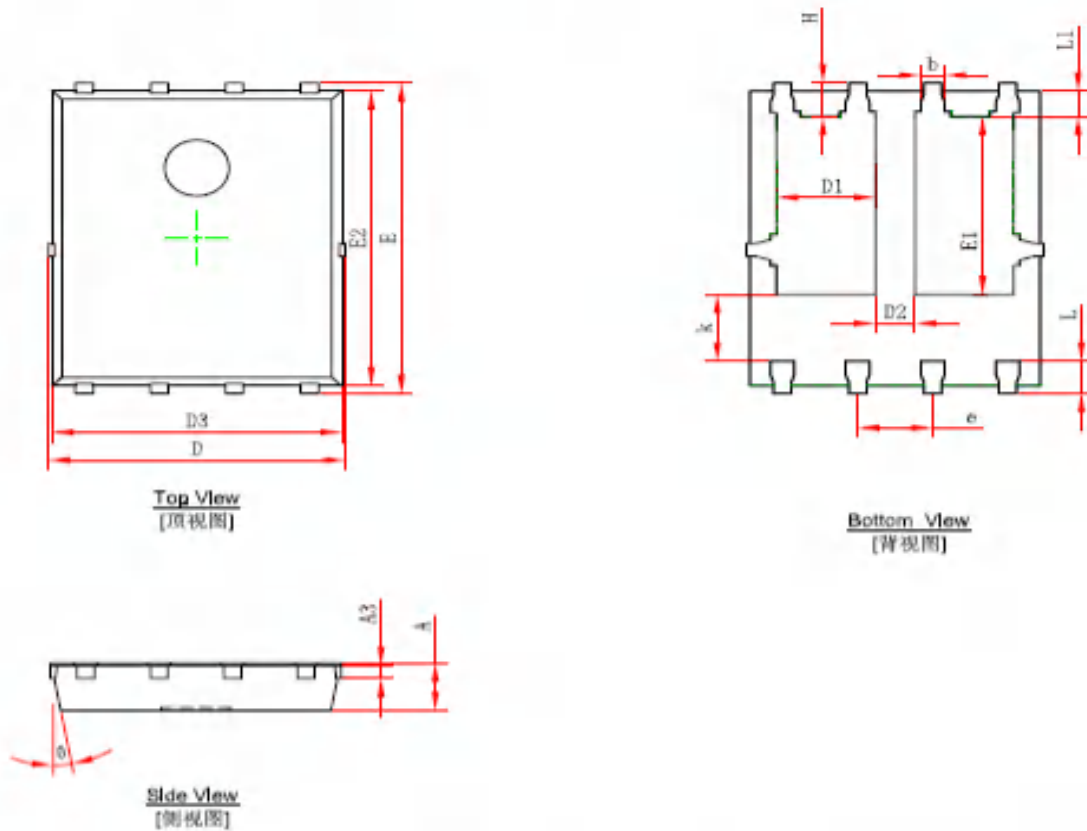


Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


PDFNWB5×6-8L-A PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254 REF.		0.010 REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	1.470	1.870	0.058	0.074
D2	0.470	0.870	0.019	0.034
E1	3.375	3.575	0.133	0.141
D3	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270 TYP.		0.050 TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°

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